

# BYV27-1GE THRU BYV27-2GE

**GLASS PASSIVATED JUNCTION**  
**ULTRAFAST EFFICIENT SILICON RECTIFIER**  
**VOLTAGE: 100 TO 200V      CURRENT: 2.0A**

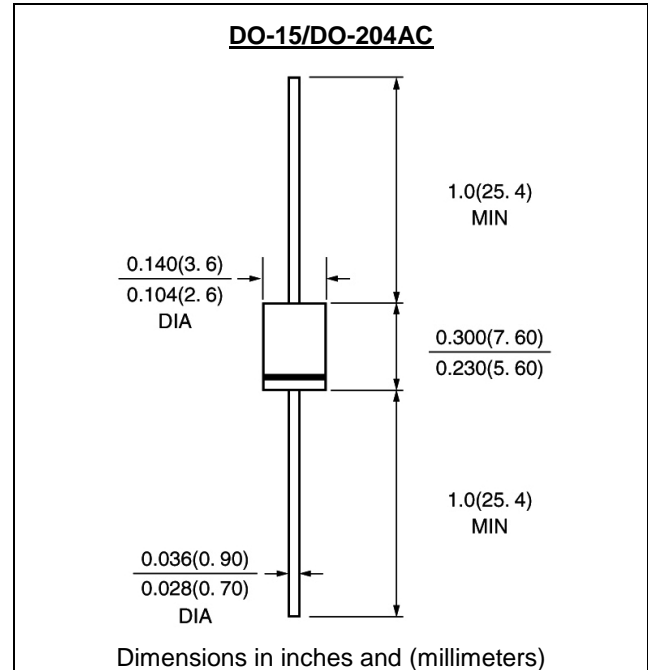


## FEATURE

Low power loss  
 High surge capability  
 Glass passivated chip junction  
 Ultra-fast recovery time for high efficiency  
 High temperature soldering guaranteed  
 250°C/10sec/0.375" lead length at 5 lbs tension

## MECHANICAL DATA

Terminal: Plated axial leads solderable per MIL-STD 202E, method 208C  
 Case: Molded with UL-94 Class V-0 recognized Flame Retardant Epoxy  
 Polarity: color band denotes cathode  
 Mounting position: any



## MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

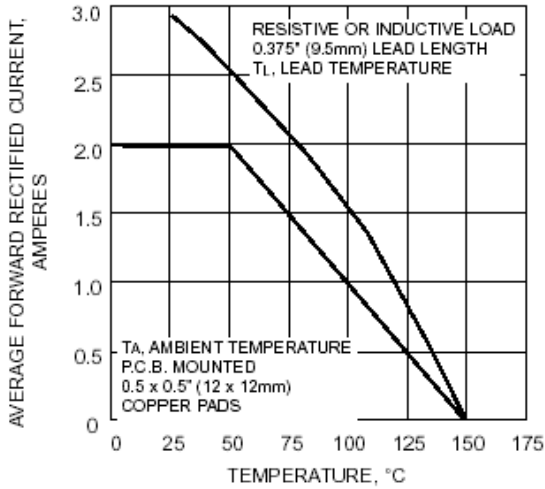
(single-phase, half-wave, 60HZ, resistive or inductive load rating at 25°C, unless otherwise stated)

|   | SYMBOL              | BYV27-1GE   | BYV27-2GE | units    |
|---|---------------------|-------------|-----------|----------|
| Maximum Recurrent Peak Reverse Voltage  | V <sub>rrm</sub>    | 100         | 200       | V        |
| Maximum RMS Voltage   | V <sub>rms</sub>    | 70          | 140       | V        |
| Maximum DC blocking Voltage   | V <sub>dc</sub>     | 100         | 200       | V        |
| Maximum Average Forward Rectified Current 3/8" lead length at Ta =55°C            | I <sub>f(av)</sub>  | 2.0         |           | A        |
| Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rated load | I <sub>fsm</sub>    | 50.0        |           | A        |
| Maximum Forward Voltage at Forward current 2.0A Peak                              | V <sub>f</sub>      | 0.98        |           | V        |
| non-repetitive peak reverse avalanche energy (Note 1)                             | E <sub>rsm</sub>    | 20          |           | mJ       |
| Maximum DC Reverse Current Ta =25°C at rated DC blocking voltage Ta =125°C        | I <sub>r</sub>      | 5.0         | 150.0     | μA<br>μA |
| Maximum Reverse Recovery Time (Note 2)  | T <sub>rr</sub>     | 25          |           | nS       |
| Typical Junction Capacitance (Note 3)   | C <sub>j</sub>      | 15          |           | pF       |
| Typical Thermal Resistance (Note 4)   | R(ja)               | 45          |           | °C/W     |
| Storage and Operating Junction Temperature  | T <sub>stg,Tj</sub> | -55 to +150 |           | °C       |

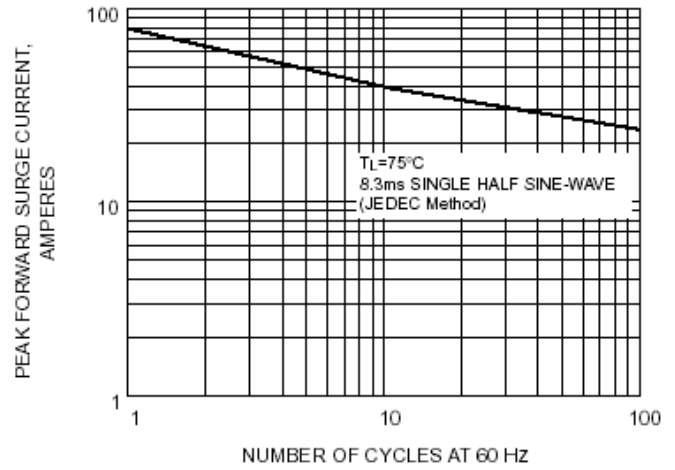
Note: 1.L = 120 mH; T<sub>j</sub> = T<sub>j</sub> max prior to surge; inductive load switched off.  
 2.Reverse Recovery Condition I<sub>f</sub> =0.5A, I<sub>r</sub> =1.0A, I<sub>rr</sub> =0.25A  
 3.Measured at 1.0 MHz and applied reverse voltage of 4.0Vdc  
 4.Thermal Resistance from Junction to Ambient at 3/8"lead length, P.C. Board Mounted

# RATINGS AND CHARACTERISTIC CURVES BYV27-1GE THRU BYV27-2GE

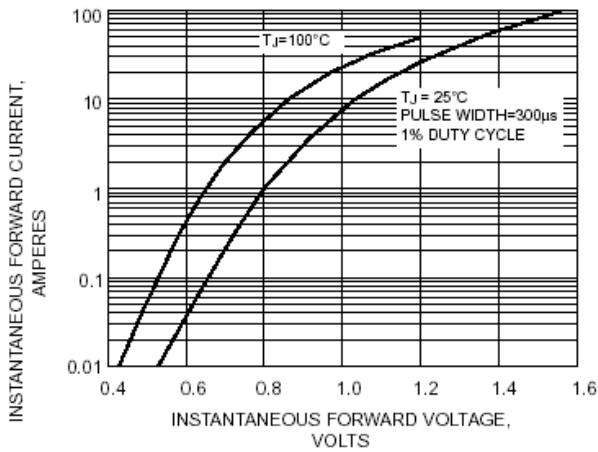
**FIG. 1 - MAXIMUM FORWARD CURRENT DERATING CURVES**



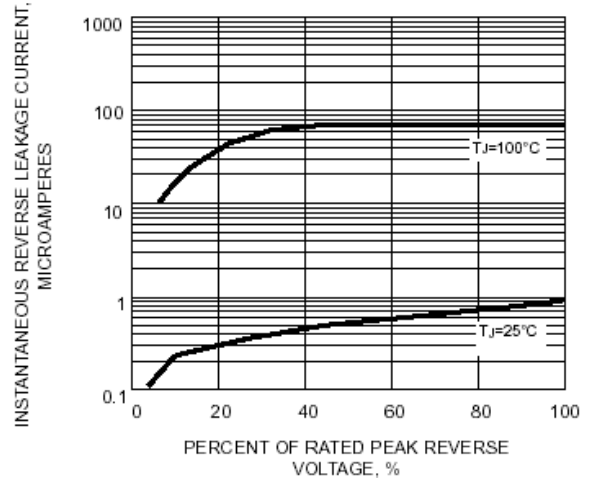
**FIG. 2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT**



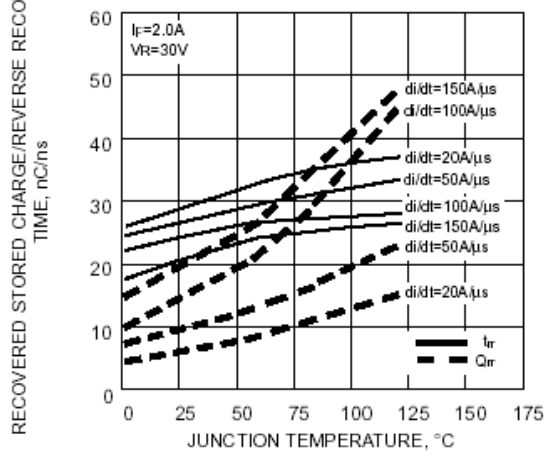
**FIG. 3 - TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS**



**FIG. 4 - TYPICAL REVERSE LEAKAGE CHARACTERISTICS**



**FIG. 5 - REVERSE SWITCHING CHARACTERISTICS**



**FIG. 6 - TYPICAL JUNCTION CAPACITANCE**

